a second semiconductor laser element disposed on top of said first semiconductor laser element, said second semiconductor laser element having an emission wavelength different from the emission wavelength of said first semiconductor laser element and a temperature dependence lower than the temperature dependence of said first semiconductor laser element.

7. (Unamended) A semiconductor laser device comprising:

a stem having a mounting surface; and

a plurality of semiconductor laser elements disposed one on top of another and directly or indirectly mounted onto the mounting surface of the stem, said plurality of semiconductor laser elements having different emission wavelengths and different temperature dependencies;

wherein said plurality of semiconductor laser elements are stacked in order of temperature dependence such that the laser chip farther from the mounting surface of the stem has a lower temperature dependence than the laser chip closer to the mounting surface of the stem.

Please add the following new claims:

8. (New) The laser device of claim 1, wherein the second laser element emits a higher wavelength than does the first laser element that is closer to the mounting surface of the stem.

9. (New) The laser device of claim 7, wherein the laser chip farther from the mounting surface emits a higher wavelength than does the laser chip closer to the mounting surface of the stem.

10. (New) A semiconductor laser device comprising:

a first semiconductor laser element supported by a mount, said first semiconductor laser element having an emission wavelength and a temperature dependence; and

a second semiconductor laser element disposed at least partially over said first semiconductor laser element and also supported by the mount, said second semiconductor laser element having an emission wavelength higher than the emission wavelength of said first semiconductor laser element and a temperature dependence lower than the temperature dependence of said first semiconductor laser element so that power of the second semiconductor laser element is less affected by a given change in temperature than power of the first semiconductor laser element which is closer to the mount.

11. (New) A semiconductor laser device comprising:

a stem including a mounting surface;

a first semiconductor laser element directly or indirectly mounted on the mounting surface of said stem, said first semiconductor laser element having an emission wavelength in a range of 640-660 nm; and